Performance

- Technology: 0.25um Power HFET
- Frequency: 1.2~1.6GHz
- P_{out}: 150W
- PAE: 55% (typ.)
- Typical Gain: 13dB
- Bias: 28V/-2.5V
- Package: Metal Ceramic

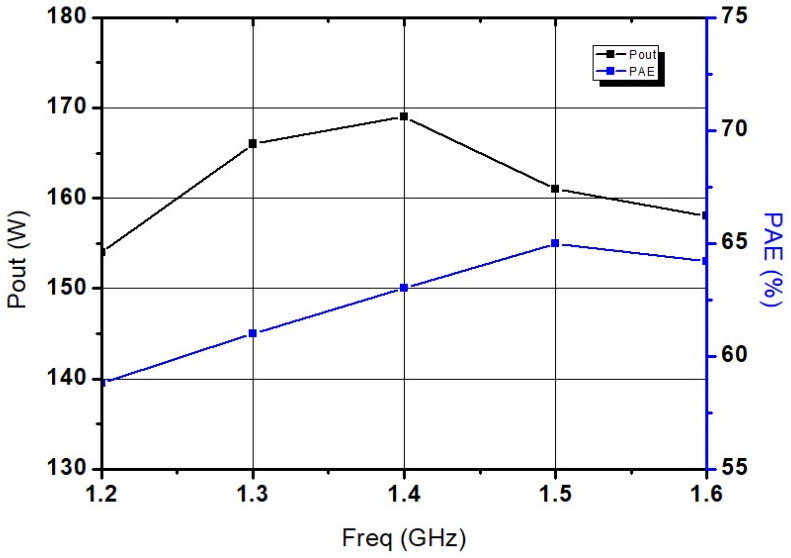
Function Diagram

Electrical Specifications (V_d=28V, Vg=-2.5V, F=1.2~1.6GHz)

Symbol	Parameter	Min	Typical	Max	Unit
Pout	Output Power	-	150	-	W
Gp	Power Gain	-	13	-	dB
η_{add}	Power Added Efficiency	-	55	-	%
△Gp	Gain Flatness	-0.5	-	+0.5	dB

Test Curves

Output Power & PAE vs. Freq

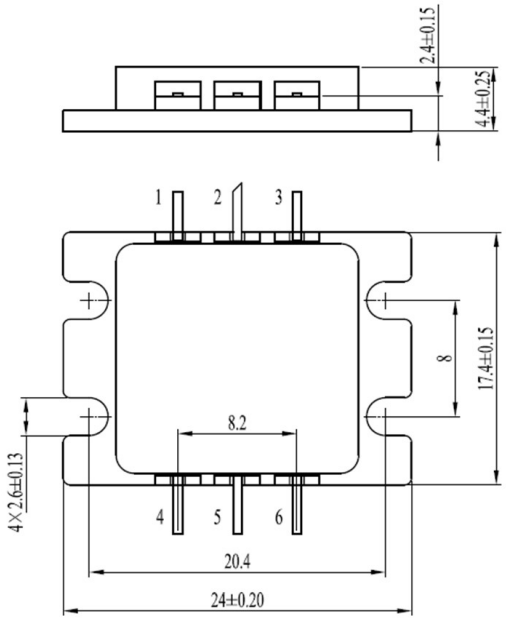


Absolute Max Ratings (T_A=25℃)

Symbol	Parameter	Value	Remark
V_D	Drain Voltage	36V	
V_G	Gate Voltage	-5V	
P_D	DC Power	125W	25℃
T_{CH}	Channel Temperature	175℃	
T_M	Mounting Temperature	300℃	1min, N_2 protection
T_{STG}	Storage Temperature	-55~175℃	

Exceeding any one or combination of these limits may cause permanent damage.

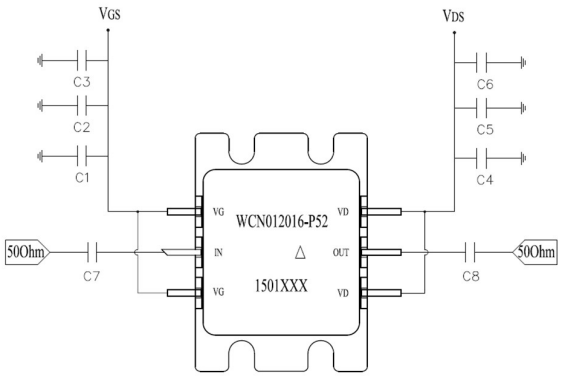
Outline Size



Pin Definition

No	Function
1,3	Vgs
2	RF input
4,6	Vds
5	RF output

Application Circuit



No	Value
C1	100 pF
C2	1000 pF
C3	47 uF
C4	100 pF
C5	1000 pF
C6	10 uF
C7	20 pF
C8	20 pF